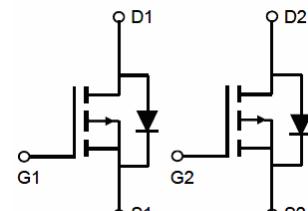
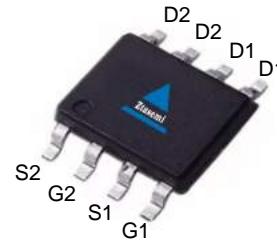


## Features

- Dual P-Channel
- Advanced Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired

$V_{DS}$	-30	V
$R_{DS(on),TYP} @ V_{GS}=-10\text{ V}$	43	mΩ
$R_{DS(on),TYP} @ V_{GS}=-4.5\text{ V}$	65	mΩ
$I_D$	-5.1	A

**SOP-8**


Part ID	Package Type	Marking	Packing
ZT4953	SOP-8	4953	4000pcs/reel

**Absolute Maximum Ratings  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (<math>T_c=25^\circ\text{C}</math> Unless Otherwise Noted)</b>				
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30	V	
$T_J$	Maximum Junction Temperature	150	°C	
$T_{STG}$	Storage Temperature Range	-55 to 150	°C	
$I_{DM}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_c=25^\circ\text{C}$	-20.4	A
<b>Mounted on Large Heat Sink</b>				
$I_D$	Drain Current-Continuous	$T_c=25^\circ\text{C}$	-5.1	A
		$T_c=100^\circ\text{C}$	-3.3	A
$P_D$	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	2.2	W
$R_{\theta JA}$	Thermal Resistance Junction-ambient	58	°C/W	

**Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ <math>T_J=25^\circ\text{C}</math> (unless otherwise stated)</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	--	--	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	--	--	-1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	--	--	$\pm 100$	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.6	-2.5	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	--	43	55	$\text{m}\Omega$
$R_{\text{DS}(\text{on})}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	--	65	90	$\text{m}\Omega$

**Dynamic Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise stated)**

$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	--	568	--	pF
$C_{\text{oss}}$	OutputCapacitance		--	96	--	pF
$C_{\text{rss}}$	ReverseTransferCapacitance		--	73	--	pF
$Q_g$	Total Gate Charge	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-5.1\text{A}, V_{\text{GS}}=-10\text{V}$	--	6.6	--	nC
$Q_{\text{gs}}$	Gate-SourceCharge		--	0.9	--	nC
$Q_{\text{gd}}$	Gate-DrainCharge		--	1.3	--	nC

**Switching Characteristics**

$T_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=-15\text{V}, I_{\text{D}}=-1\text{A}, R_{\text{G}}=2.5\Omega, V_{\text{GS}}=-10\text{V}$	--	14	--	ns
$T_r$	Turn-on Rise Time		--	60	--	ns
$T_{\text{d}(\text{off})}$	Turn-Off Delay Time		--	18	--	ns
$T_f$	Turn-Off Fall Time		--	10	--	ns

**Source- Drain Diode Characteristics@  $T_J = 25^\circ\text{C}$  (unless otherwise stated)**

$I_{\text{SD}}$	Source-Drain Current (Body Diode)		--	--	-5.1	A
$V_{\text{SD}}$	Forward on voltage	$I_{\text{S}}=-5.1\text{A}, V_{\text{GS}}=0\text{V}$	--	--	1.2	V

**Notes:**

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$ , Duty Cycle $\leq 2\%$



## Typical Performance Characteristics

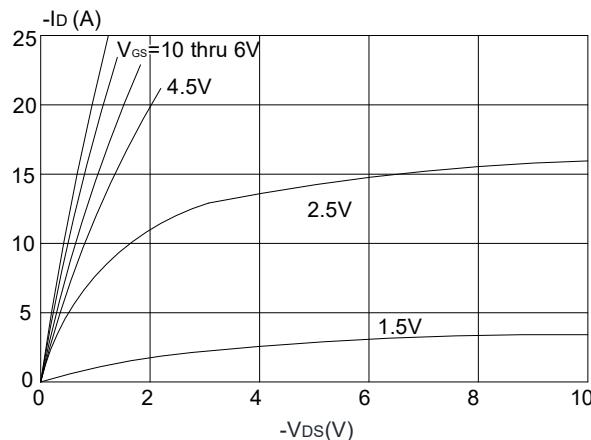


Figure 1: Output Characteristics

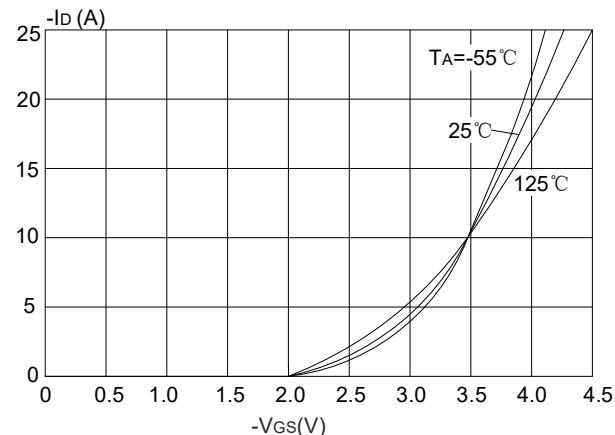


Figure 4: Typical Transfer Characteristics

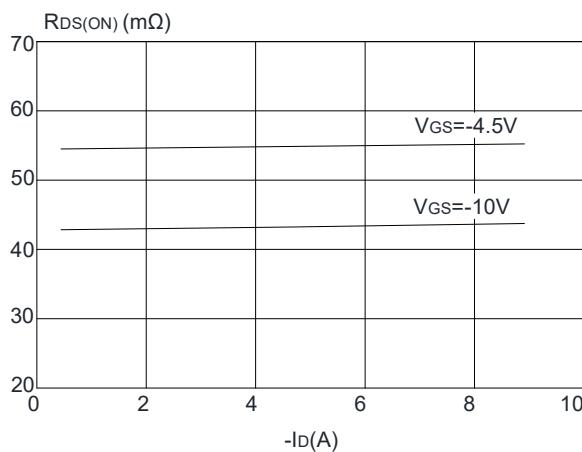


Figure 2: On-resistance vs. Drain Current

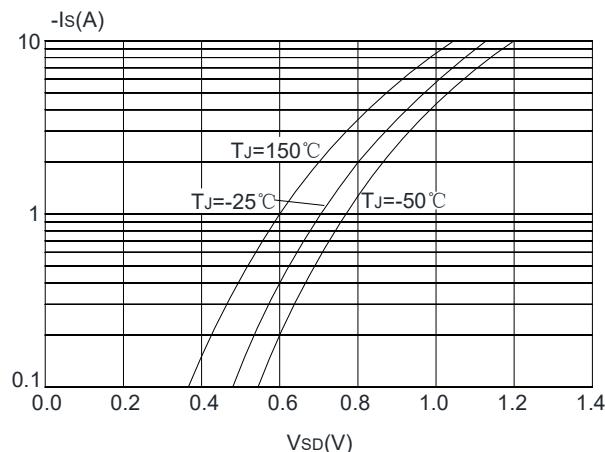


Figure 5: Body Diode Characteristics

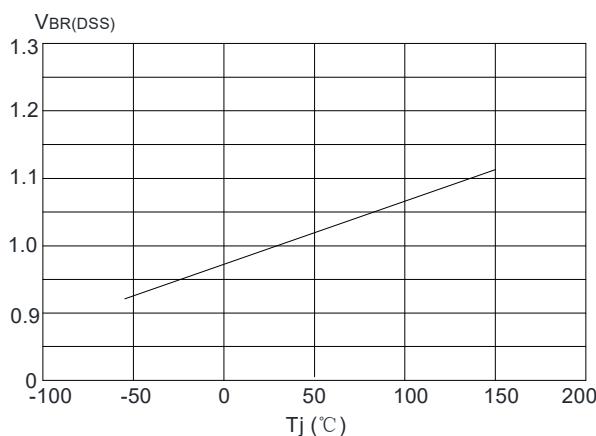


Figure 3: Normalized Breakdown Voltage vs. Junction Temperature

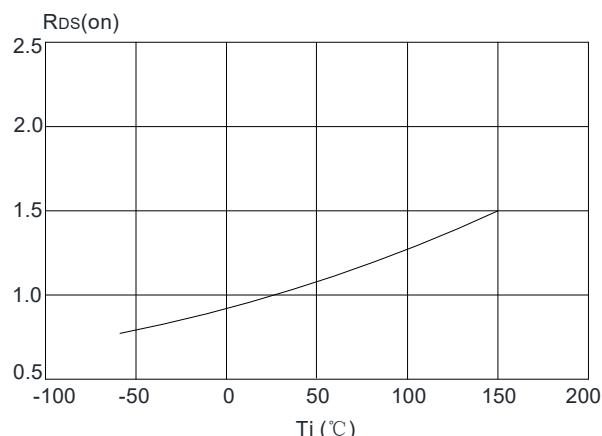
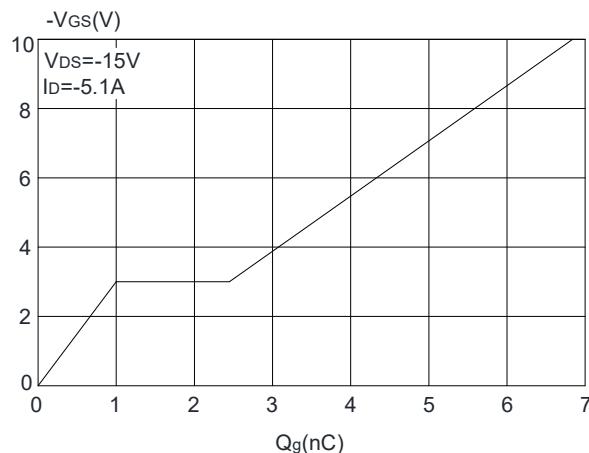
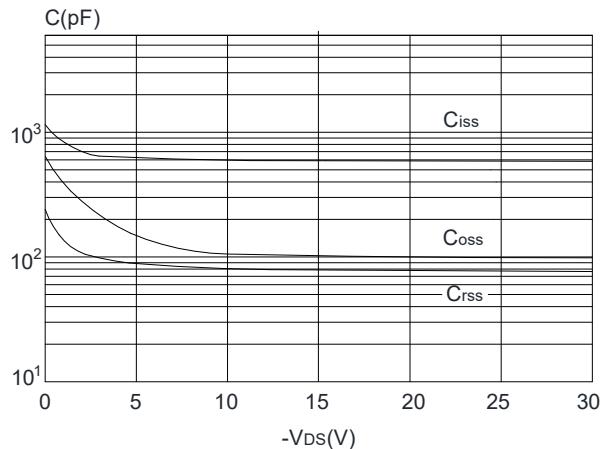


Figure 6: Normalized on Resistance vs. Junction Temperature

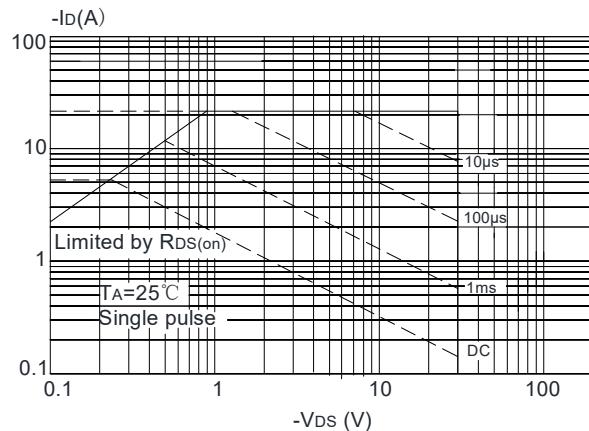
## Typical Performance Characteristics



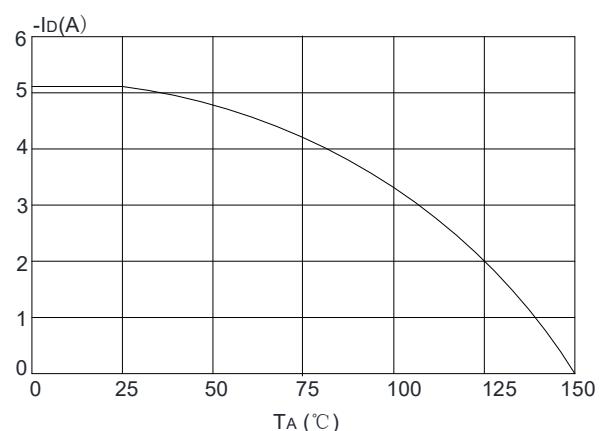
**Figure 7:** Gate Charge Characteristics



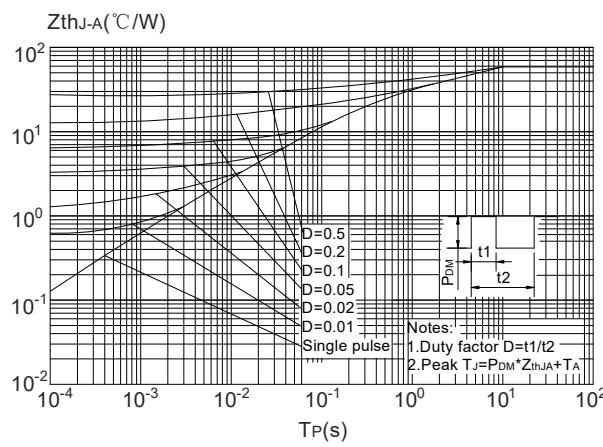
**Figure 9:** Capacitance Characteristics



**Figure 8:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

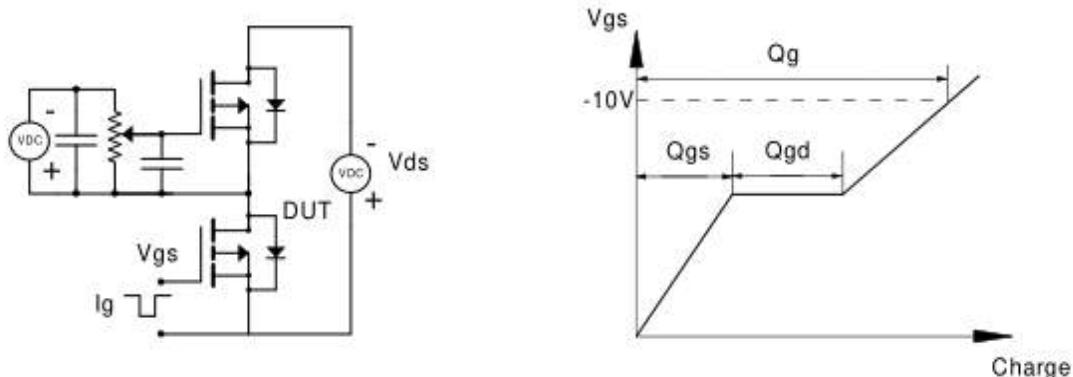


**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

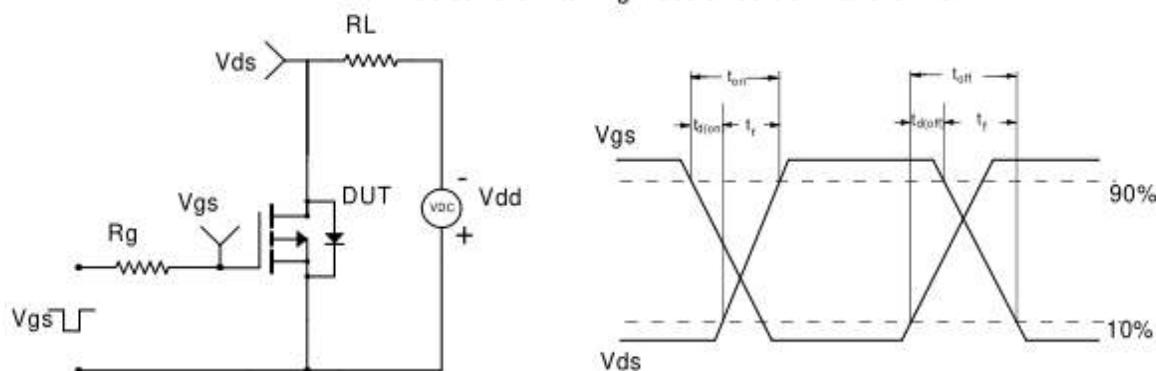


## Test Circuit

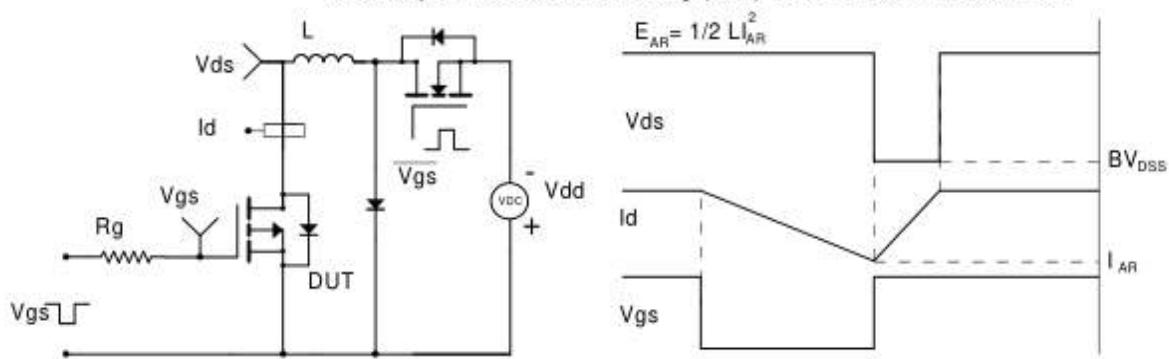
Gate Charge Test Circuit & Waveform



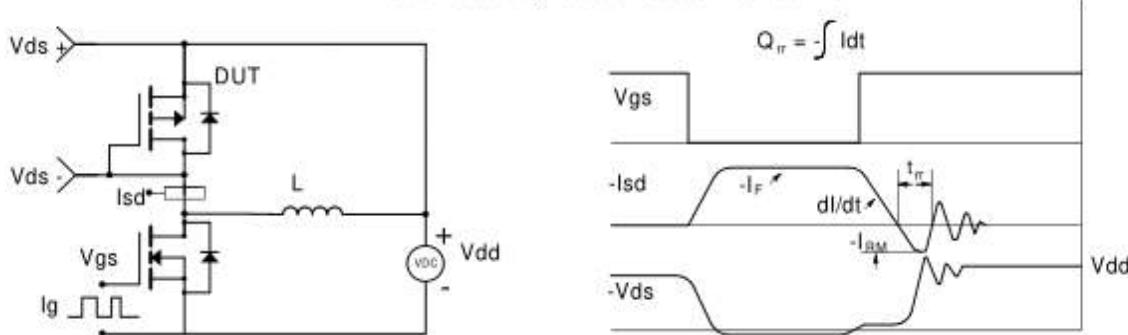
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

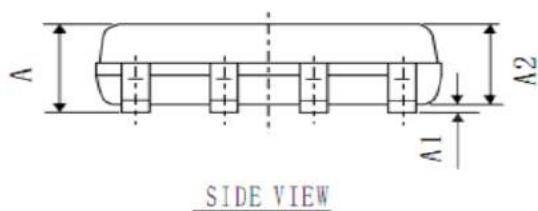
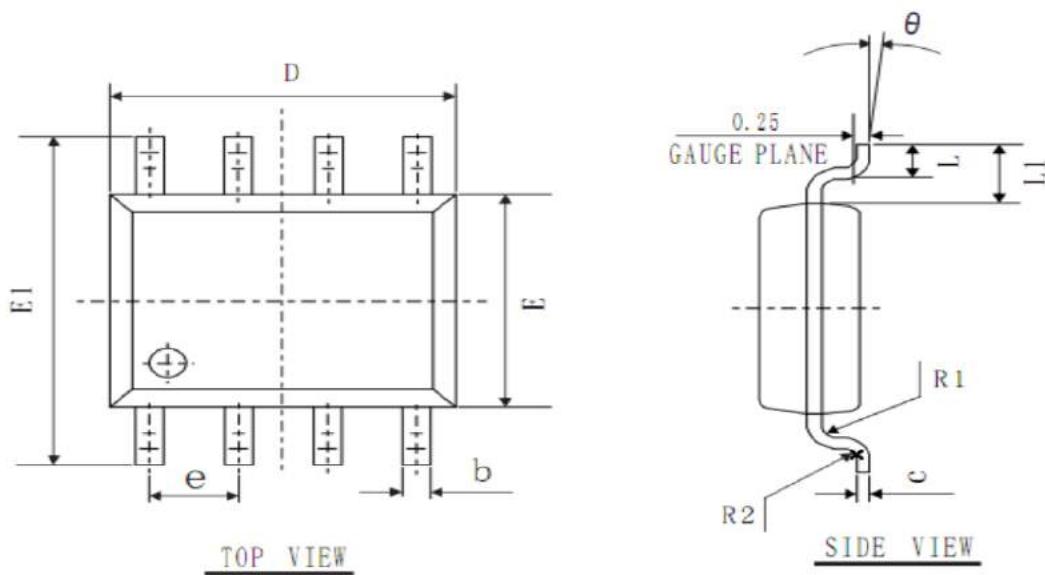


Diode Recovery Test Circuit & Waveforms





## SOP-8 Package Information



COMMON DIMENSIONS  
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

## Customer Service

### Sales and Service:

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